AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (Previously Presented): A semiconductor device, comprising:

an insulating substrate having a surface on which a first SiO_2 film is formed;

a single-crystal silicon thin film having bonded thereto a second SiO_2 film, which single-crystal silicon thin film is bonded with the insulating substrate on a partial region of the insulating substrate via the first and second SiO_2 films; and

a non-single-crystal silicon thin film comprising an active area of a transistor and formed on the insulating substrate in a region where the single-crystal silicon thin film is not bonded with the insulating substrate, which non-single-crystal silicon thin film is formed on the insulating substrate via the first SiO_2 film and a third SiO_2 film,

wherein the second SiO_2 film and the third SiO_2 film are of different thicknesses.

Claim 2 (Canceled).

Claim 3 (Previously Presented): The semiconductor device as defined in claim 1, wherein the single-crystal silicon thin film has a thickness of not more than about 70nm.

Claim 4 (Previously Presented): The semiconductor device as defined in claim 1, wherein the single-crystal silicon thin film has a thickness of not more than about 20nm.

Claim 5 (Previously Presented): The semiconductor device as defined in claim 1, wherein the non-single-crystal silicon thin film comprises polycrystalline silicon.

Claim 6 (Previously Presented): The semiconductor device as defined in claim 1, wherein the non-single-crystal silicon thin film comprises continuous grain silicon.

Claim 7 (Previously Presented): The semiconductor device as defined in claim 1, wherein the non-single-crystal silicon thin film comprises amorphous silicon.

Claim 8 (Previously Presented): The semiconductor device as defined in claim 7, wherein a non-single crystal silicon thin-film transistor, which includes a gate insulating film made up of at least one insulating film including silicon nitride, is formed using the amorphous silicon thin film.

Claim 9 (Previously Presented): A semiconductor device, comprising:

an insulating substrate having a surface on which a first SiO_2 film is formed;

a single-crystal silicon thin film having bonded thereto a second SiO_2 film, which single-crystal silicon thin film is bonded with the insulating substrate on a partial region of the insulating substrate via the first and second SiO_2 films; and

a non-single-crystal silicon thin film formed on the insulating substrate in a region where the single-crystal silicon thin film is not bonded with the insulating substrate, which non-single-crystal silicon thin film is formed on the insulating substrate via the first SiO_2 film and a third SiO_2 film,

wherein the second SiO_2 film and the third SiO_2 film are of different thicknesses, and

wherein a transistor formed using the single-crystal silicon thin film is arranged such that, from an insulating substrate side, a gate electrode, a gate insulating film, and the single-crystal silicon thin film are formed in this order.

Claim 10 (Previously Presented): The semiconductor device as defined in claim 9, wherein at least a part of the transistor formed using the single-crystal silicon thin film includes

an interlayer insulating film and metal interconnects provided further on the single-crystal silicon thin film.

Claim 11 (Previously Presented): The semiconductor device as defined in claim 9, wherein the transistor formed using the single-crystal silicon thin film is arranged such that, from an insulating substrate side, an interlayer insulating film, a metal interconnects layer, an interlayer insulating film, a gate electrode, a gate insulating film, and the single-crystal silicon thin film are formed in this order, and in at least a part of the transistor, an interlayer insulating film and metal interconnects are further provided on the single-crystal silicon thin film.

Claim 12 (Previously Presented): The semiconductor device as defined in claim 1, wherein the insulating substrate comprises a high strain point glass including an alkaline-earth alumino-borosilicate glass.

Claim 13 (Previously Presented): The semiconductor device as defined in claim 1, wherein the insulating substrate comprises any one of a barium borosilicate glass, a barium alumino-borosilicate glass, an alkaline-earth alumino-borosilicate glass, a borosilicate glass, an alkaline-earth-zinc-lead-alumino-borosilicate glass, and an alkaline-earth-lead-alumino-borosilicate glass.

Claim 14 (Previously Presented): The semiconductor device as defined in claim 1, wherein a difference of linear expansion between the insulating substrate and the single-crystal silicon thin film is about not more than 250ppm at temperatures in a range between substantially room temperature and 600°C.

Claim 15 (Previously Presented): The semiconductor device as defined in claim 1, wherein the insulating substrate comprises a high strain point glass whose strain point is not less than 500°C.

Claims 16-50 (Canceled).

Claim 51 (Previously Presented): A semiconductor device, comprising:

an insulating substrate having a surface on which a first SiO_2 film is formed;

a single-crystal silicon thin film having bonded thereto a second SiO_2 film, which single-crystal silicon thin film is bonded to the insulating substrate via the first and second SiO_2 films, the single-crystal silicon thin film having a substantially uniform thickness and a substantially damage-free surface; and

a non-single-crystal silicon thin film comprising an active area of a transistor and formed on the insulating substrate in a region where the single-crystal silicon thin film is not bonded with the insulating substrate, which non-single-crystal silicon thin film is formed on the insulating substrate via the first SiO_2 film and a third SiO_2 film,

wherein

the second SiO_2 film and the third SiO_2 film are of different thicknesses.

Claim 52 (Previously Presented): The semiconductor device as defined in claim 51, further comprising:

transistor elements formed from the single-crystal silicon thin film.

Claim 53 (Previously Presented): A semiconductor device, comprising:

an insulating substrate having a surface on which a first SiO_2 film is formed;

a single-crystal silicon thin film having bonded thereto a second SiO_2 film, which single-crystal silicon thin film is bonded to the insulating substrate via the first and second SiO_2 films, the single-crystal silicon thin film having a substantially uniform thickness and a substantially damage-free surface;

a non-single-crystal silicon thin film formed on the insulating substrate in a region where the single-crystal silicon thin film is not bonded with the insulating substrate, which non-single-crystal silicon thin film is formed on the insulating substrate via the first SiO_2 film and a third SiO_2 film; and

transistor elements formed from the single-crystal silicon thin film,

wherein the second SiO_2 film and the third SiO_2 film are of different thicknesses, and

wherein the transistor elements are arranged such that, from an insulating substrate side, a gate electrode, a gate insulating film, and the single-crystal silicon thin film are formed in this order.

Claim 54 (Previously Presented): A semiconductor device, comprising:

an insulating substrate having a surface on which a first SiO_2 film is formed; and

a single-crystal silicon thin film bonded with the insulating substrate on a partial region of the insulating substrate,

wherein the single-crystal silicon thin film has a substantially uniform thickness and has a surface substantially free of damage,

the single-crystal silicon thin film has bonded thereto a second SiO_2 film,

the surface of the insulating substrate, where the first SiO_2 film is formed, is bonded with the single-crystal silicon thin film, where the second SiO_2 film is formed, and

a transistor formed using the single-crystal silicon thin film is arranged such that, from an insulating substrate side, a gate electrode, a gate insulating film, and the single-crystal silicon thin film are formed in this order.

Claim 55 (Previously Presented): A semiconductor device, comprising:

an insulating substrate having a surface on which a first SiO_2 film is formed;

a single-crystal silicon thin film bonded to the insulating substrate, the single-crystal silicon thin film having a substantially uniform thickness and a substantially damage-free surface; and

transistor elements formed from the single-crystal silicon thin film,

wherein

the single-crystal silicon thin film has bonded thereto a second SiO_2 film,

the surface of the insulating substrate on which the first SiO_2 film is formed is bonded with the second SiO_2 film thereby bonding the single-crystal silicon thin film to the insulating substrate,

the bonded single-crystal silicon thin film is disposed on only part of the insulating substrate on which the first SiO_2 film is formed, and

the transistor elements are arranged such that, from an insulating substrate side, a gate electrode, a gate insulating film, and the single-crystal silicon thin film are formed in this order.

Claims 56 and 57(Canceled).

Claim 58 (Previously Presented): The semiconductor device as claimed in claim 1, wherein the non-single-crystal silicon thin film is not formed on the insulating substrate via the second SiO_2 film.

Claim 59 (Previously Presented): The semiconductor device as claimed in claim 1, wherein the second SiO_2 film is provided in an area corresponding to an area of the single-crystal silicon thin film.

Claims 60 and 61(Canceled).

Claim 62 (Previously Presented): The semiconductor device as claimed in claim 51, wherein the non-single-crystal silicon thin film is not formed on the insulating substrate via the second SiO_2 film.

Claim 63 (Previously Presented): The semiconductor device as claimed in claim 51, wherein the second SiO_2 film is provided in an area corresponding to an area of the single-crystal silicon thin film.